

DESCRIPTION

The CENTRAL SEMICONDUCTOR CMPT4033 type is an PNP silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for very high current, general purpose amplifier applications.
Marking Code is C4A.

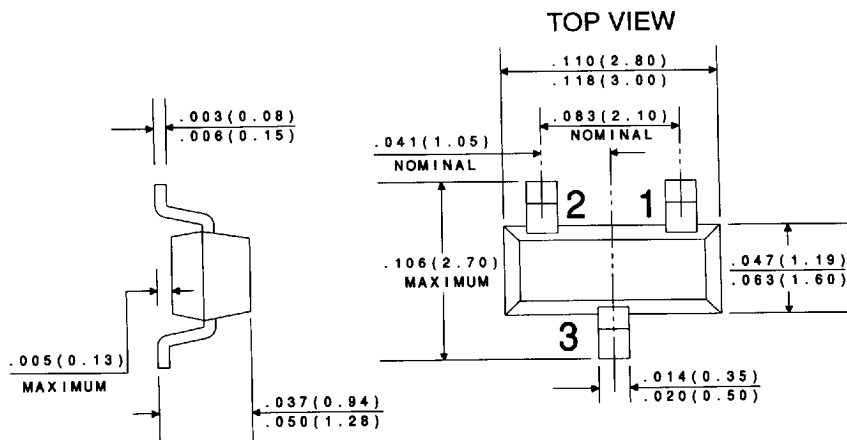
MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CB0}	80	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	500	mA
Collector Current (Peak)	I_{CM}	1.0	A
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	Θ_{JA}	357	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CB0}	$V_{CB}=60\text{V}$		50	nA
I_{EBO}	$V_{EB}=5.0\text{V}$		10	nA
BV_{CB0}	$I_C=10\mu\text{A}$	80		V
BV_{CEO}	$I_C=10\text{mA}$	80		V
BV_{EBO}	$I_E=10\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		0.15	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		0.50	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		0.90	V
$V_{BE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		1.10	V
h_{FE}	$V_{CE}=5.0\text{V}, I_C=0.1\text{mA}$	75		
h_{FE}	$V_{CE}=5.0\text{V}, I_C=100\text{mA}$	100	300	
h_{FE}	$V_{CE}=5.0\text{V}, I_C=500\text{mA}$	70		
f_T	$V_{CE}=10\text{V}, I_C=50\text{mA}, f=1.0\text{MHz}$	100		MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		20	pF
C_{ib}	$V_{EB}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$		110	pF

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR

DATA
SHEET

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